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We have considered the response at two energies corresponding to two plateaus in the quantum Halle ect. Since the therm oelectric power involves the derivative of conductivity with respect to energy, we introduce the concept of a line width and hence an activation energy. We then use the Hall conductivity to de ne the therm oelectric power at the centre of two plateaus, which is found to vary monotonically as  $T^2$  at low tem – peratures with xed magnetic eld. At elivated tem peratures, the therm oelectric power varies as T exp(-=k<sub>B</sub>T).

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## 1. Introduction

The phenom enon of quantum Halle ect has been described for a long tim e[1,2]. The them oelectric power involves the derivative of conductivity as a function of energy so that at the plateau in the Hall resistivity, where energy is xed, it is not well de ned. On the other hand, if we look at the centre of two plateaus, at a xed magnetic eld, we can de ne this derivative by using a relaxation process. The therm oelectric power can then give inform ation about the relaxation mechanism in the quantum Halle ect away from the plateaus. In the transverse resistivity there are minim a at the same magnetic elds where there are plateaus in the longitudinal resistivity. These elds are described by integers as well as fractions which are predicted by us[3].

In this communication, we obtain the therm oelectric power at the centre of two plateaus. This is an important point because the system becomes metallic just before the plateaus and hence there is a peak in the resistivity at a point in the centre of two plateaus. The system is some times referred to as \insulator" near the peak. Thus we are able to not the therm oelectric power in the insulating phase.

## 2. Theory

We consider a three level system in which the energies are labeled as  $E_0$ ,  $E_1$  and  $E_2$ . It absorbs energies  $E_2$ - $E_0$  and  $E_1$ - $E_0$  so that there are two lines in the absorption as a function of energy. If these lines are far apart, there is no overlap and hence there is no region where the absorption depends on line width. We select a problem where there is a region in which the absorption depends on the line width. The width of the line at  $E_1$  is  $_1$  and that at  $E_2$  is  $_2$ . The response function in this case is given by,

$$" = \frac{1}{f(E - E_1) = hg^2 + (I_1)^2} + \frac{2}{f(E - E_2) = hg^2 + (I_2)^2}$$
(1)

If  $E_2 = E_1 >> h_1$ , the lines are well resolved and peaked at well de ned energies such as  $E_1$  and  $E_2$ . On the other hand if  $E_2 = E_1 < h_1$ , the lines overlap and there is absorption in the centre of two spectral lines. Since we are interested in the therm oelectric power in the centre of two lines, we consider the case of overlap between two lines. We suppose that the two lines are separated by 1 such that 1 is smaller than either 1 or 2, i.e.,

$$\mathbf{E}_2 \quad \mathbf{E}_1 = \ _1 \tag{2}$$

$$_{1} < < _{1}$$
 (3)

$$_{1} < < _{2}$$
: (4)

 $AtE = E_1$ , the rst term in the response function is peaked so that the response becomes,

$$" = \frac{1}{1} + \frac{2}{f(E_1 - E_2) = hg^2 + (-2)^2}$$
(5)

but the line at  $E_2$  is very near the one at  $E_1$  so that the lines overlap. Substituting (2) in (5) we nd,

$$" = \frac{1}{1} + \frac{2}{(1-h)^2 + (1-2)^2}:$$
 (6)

For convenience of algebra, we assume  $_{1}$  '  $_{2}$  so that the centre of the lines between  $E_{1}$  and  $E_{2}$  is located at  $E_{1} + \frac{1}{2}_{1}$ . If the relaxation occurs due to interaction with phonons, the width depends on the phonon correlation function, 2n + 1, where  $n = [\exp(=k_{B}T) \ 1]^{1}$ . It is also possible to say that n '  $\exp(=k_{B}T)$  at low tem peratures so that becomes the activation energy,

$$_{1} = c_{1} (2n + 1)' 2c_{1} exp(=k_{B}T)$$
 (7)

In the symmetric case,

$$_{1} = _{1}$$
: (8)

Let us consider the old Halle ect. In the quantum Halle ect the conductivity is quantized as  $= ie^2 = h$  where im ay be an integer or a fraction. We believe that this fraction depends on spin. If there are two plateaus, they occur at  $i = _1$  and  $i = _2$ . The conductivity is quantized at both  $_1$  as well as at  $_2$  but we are neither interested in quantization at  $_1$  nor at  $_2$ . We are interested in the point which is exactly in the middle of  $_1$  and  $_2$  so that there is no quantization at this point.

The current is determined by j = nev where n is the concentration of electrons, e the charge and v the velocity. We replace the charge by energy  $E_c = E_F + \frac{3}{2}k_B T$  and devide the resulting expression by the current to de ne the Peltier coe cient,

$$= \frac{E_{c}}{e} \frac{E_{F} + \frac{3}{2}k_{B}T}{e}$$
(9)

where  $E_c$  is the electron energy in the conduction band. The negative sign in the above has come from the sign of the charge, -e. The therm coelectric power, S, may be de ned as,

$$=$$
 ST (10)

where T is the tem perature. If F j is the electric eld, another de nition of the therm oelectric power is obtained by,

$$f j = SgradT$$
 (11)

or

$$S = \frac{\text{Fj}}{\text{gradT}};$$
 (12)

We can replace the grad by d=dx but then the tem perature gradient has to be evaluated. Apparently, M ott has solved [4] this problem by de ning the therm celectric power by using the energy derivative of the logarithm of the conductivity,

$$S = \frac{{}^{2}k_{B}^{2}T}{3e}\frac{d}{dE}\ln \dot{E}_{E_{F}}: \qquad (13)$$

This means that we should know the conductivity as a function of energy, then only we can use the M ott form ula. A swe described above, we are interested in a point which is m id way between two quantized values, we use the old result according to which the H all resistivity is = nec=B and hence the H all conductivity is,

$$=\frac{nec}{B}$$
(14)

where n is the electron concentration, e is the charge, B is the magnetic eld and c is the velocity of light. The transition energies in the system described above are  $E_1 = \frac{1}{2}g_BB_1$  and  $E_2 = \frac{1}{2}g_BB_2$ . Our transitions occur at  $E_1$  and  $E_2$  and the centre is at  $E_1 + \frac{1}{2}_1$ . Thus there is quantization at  $E_1$  and at  $E_2$  but not at  $E_1 + \frac{1}{2}_1$ . Therefore, the conductivity becomes,

$$=\frac{1}{2}g_{B}\operatorname{nec}\frac{1}{E}$$
(15)

where  $E = \frac{1}{2}g_{B}B$ . Taking the logarithm of conductivity, we obtain,

$$\ln = \ln \left(\frac{1}{2}g_{B} \operatorname{nec}\right) \quad \ln E \tag{16}$$

so that

$$\frac{d}{dE}\ln = \frac{d}{dE}\ln E = \frac{1}{E}:$$
(17)

If the conductivity is therm ally activated,

$$= _{o} \exp (E = k_{B} T)$$
 (18)

we obtain,

$$\frac{\mathrm{d}}{\mathrm{dE}}\ln = \frac{1}{\mathrm{k}_{\mathrm{B}}\mathrm{T}}:$$
(19)

In this case, the therm oelectric power will be independent of tem perature. Therefore, we do not consider this case but we consider the therm ally activated relaxation rate. We go back to the M ott form ula to nd the therm oelectric power as,

$$S = -\frac{{}^{2}k_{B}^{2}T}{3e}\frac{1}{E}$$
 (20)

W here the negative sign means that power reduces as the energy is increased. W hen energy is either  $E_1$  or  $E_2$ , the conductivity is quantized but at them id point,  $E = E_1 + \frac{1}{2}_{1}$ , the conductivity is not quantized so that at this point,

$$S = \frac{{}^{2}k_{B}^{2}T}{3eE_{1}(1+\frac{1}{2}\frac{1}{E_{1}})};$$
(21)

If  $_1$  is very small compared with  $E_1$  we can write the term in the denominator as,

$$S = \frac{1}{6E_{1}^{2}} \frac{^{2}k_{B}^{2}T}{3E_{1}} - \frac{^{2}k_{B}^{2}T}{3E_{1}}$$
(22)

Thus there is a large negative term which is linear in T and a small correction which depends on the relaxation [5]. The distance  $\frac{1}{2}$  1 m ust be equal to half width so that,

$$_{1} = \frac{1}{2_{1}} = c_{1} (2n + 1)$$
: (23)

If the system is therm ally activated,  $2n + 1' 2n' 2\exp(-k_B T)$ . Therefore, the rst term in the therm oelectric power varies as,

$$S_{1} = \frac{{}^{2}k_{B}^{2} T c_{1} (2n + 1)}{6eE_{1}^{2}} \prime \frac{{}^{2}k_{B}^{2} c_{1} T exp(=k_{B} T)}{3eE_{1}^{2}}$$
(24)

in which the tem perature dependence is determ ined by

$$S_1 ' c_2 T \operatorname{coth} \frac{1}{2k_B T}$$
 (25)

which at high tem peratures varies as,

$$S_1 ' \frac{2c_2k_B T^2}{2}$$
: (26)

There is also a large negative term ,

$$S = S_1 + S_2$$
 (27)

$$S_{2} = \frac{{}^{2}k_{B}^{2}T}{3eE_{1}}:$$
 (28)

Thus we have two terms in the therm oelectric power. One of these terms is negative and linear in temperature. This describes the emission of power under favourable conditions such as large relaxation times in the excited states. The other term is positive and depends approximately on  $T^2$ . It may be described as  $T \coth(=2k_B T)$ . It is known that relaxation in quantum Hall e ect is thermally activated so that the therm opower may appear as  $T \exp(=k_B T)$  as given by (24). In these results, the magnetic eld is held constant so that there is no phase transition by varying temperature. The variation of conductivity as a function of length or thickness of the sam ple is well known and it is related to a critical exponent. Polyakov and Shklovskii[6] have treated  $_1$  or an equivalent quantity as if there is a phase transition with a critical tem perature. In that case, the width is described by \scaling exponents",

where '0.4. It has been possible to correlate the exponent with which describes the coherence length. The band lling factor is called and the coherence length varies as,

$$() = (0)j_{0}j$$
 (30)

with = 2.3 or = 1 = = 0.435. Long time ago [5], the value of was thought to be 0.5. We write the scaling width as,

$$_{1} = c_{2}T \tag{31}$$

which shows that the positive term of the therm oelectric power varies as,

$$S_{1} = \frac{{}^{2}k_{B}^{2}C_{2}}{6eE_{1}^{2}}T^{+1}$$
(32)

so that the exponent +1 can be determ ined from the therm coelectric power as a function of temperature. The critical exponents are a characteristic of a phase transition. When  $T_c$  '0, (T  $T_c$ ) = T so that Polyakov's result is applicable to a phase transition at zero temperature. When we go from one level to another, we call it a phase transition. However, if we keep the magnetic eld a constant at the middle of two plateaus, then there is no phase transition and we need not expect any critical exponent.

Possanzini et al[7] have measured the them oelectric power for two di erent densities. In both the cases, the them oelectric power monotonically increases with increasing temperature from 0.4 to 4 K. An e ort is made to t the data with  $S = T^{1=3} + T^4$  which is interpreted to arise from a variable range hopping model or from  $S_{xx} = + T^4$ . Naturally, a term can be added in which the exponent has any value between 1/3 and 4 without disturbing the agreement between the model and the data. The expression (26) shows that the therm oelectric power varies as  $T^2$ . When the magnetic eld is kept constant and the temperature is varied, it is reasonable to expect that there is no phase transition so the therm oelectric power varies as  $T^2$ . At a temperature of 0.32 K, the largest positive value of the diagonal therm oelectric power is about 5 V/K and at very sm allm agnetic elds, the value is negative of the order of 10 V/K. Thus these observed features are in accord with the theoretical expressions.

3. Conclusions.

In conclusions,we nd that when eld is xed in between two plateaus, the therm oelectric power varies as  $T^2$  at low temperatures. At slightly elivated temperatures,we expect a therm ally activated relaxation process so that  $T \exp(=k_B T)$  type variation is predicted.

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